

Dimitrios Velessiotis

List of Publications by Year in descending order

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18
papers

248
citations

1163117

8
h-index

996975

15
g-index

18
all docs

18
docs citations

18
times ranked

350
citing authors

#	ARTICLE	IF	CITATIONS
1	Substrate damage in ion-implanted (100) germanium after extended ms flash lamp annealing: Origins and suppression. <i>Materials Science in Semiconductor Processing</i> , 2021, 122, 105477.	4.0	0
2	(Invited) Issues with n-type Dopants in Germanium. <i>ECS Transactions</i> , 2018, 86, 51-58.	0.5	4
3	Phosphorous Diffusion in N2+-Implanted Germanium during Flash Lamp Annealing: Influence of Nitrogen on Ge Substrate Damage and Capping Layer Engineering. <i>ECS Journal of Solid State Science and Technology</i> , 2017, 6, P418-P428.	1.8	5
4	Emergence of ambient temperature ferroelectricity in meso-tetrakis(1-methylpyridinium-4-yl)porphyrin chloride thin films. <i>Applied Physics Letters</i> , 2013, 103, 022908.	3.3	5
5	Conduction mechanisms in tungsten-polyoxometalate self-assembled molecular junctions. <i>Microelectronic Engineering</i> , 2012, 97, 150-153.	2.4	2
6	Molecular junctions made of tungsten-polyoxometalate self-assembled monolayers: Towards polyoxometalate-based molecular electronics devices. <i>Microelectronic Engineering</i> , 2011, 88, 2775-2777.	2.4	17
7	Hybrid organic-inorganic materials for molecular proton memory devices. <i>Organic Electronics</i> , 2009, 10, 711-718.	2.6	8
8	Molecular nanodevices based on functionalized cyclodextrins. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008, 205, 2532-2535.	1.8	2
9	Molecular Storage Elements for Proton Memory Devices. <i>Advanced Materials</i> , 2008, 20, 4568-4574.	21.0	36
10	Vertical devices of self-assembled hybrid organic/inorganic monolayers based on tungsten polyoxometalates. <i>Microelectronic Engineering</i> , 2008, 85, 1399-1402.	2.4	54
11	Compound polymeric materials in molecular nanodevices: electrical behavior of zero-dimension semiconducting inorganic molecules embedded in a polymer substrate. <i>Journal of Physics: Conference Series</i> , 2005, 10, 93-96.	0.4	0
12	Tungstate polyoxometalates as active components of molecular devices. <i>Journal of Applied Physics</i> , 2005, 98, 084503.	2.5	22
13	Transport properties of polyoxometalate containing polymeric materials. <i>Synthetic Metals</i> , 2003, 138, 267-269.	3.9	8
14	Tunneling transport in polyoxometalate based composite materials. <i>Applied Physics Letters</i> , 2003, 83, 488-490.	3.3	47
15	Application of the partial wave expansion method in 3-D low energy electron beam lithography simulation. <i>Microelectronic Engineering</i> , 2001, 57-58, 297-302.	2.4	4
16	Development mechanism study by dissolution monitoring of positive methacrylate photoresists. <i>Microelectronic Engineering</i> , 2000, 53, 489-492.	2.4	25
17	Aqueous base development and acid diffusion length optimization in negative epoxy resist for electron beam lithography. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2000, 18, 3431.	1.6	9
18	Post-metallization annealing and photolithography effects in p-type Ge/Al2O3/Al MOS structures. <i>ECS Journal of Solid State Science and Technology</i> , 0, , .	1.8	0